SCIENCESPRINGDAY



Material Science Department - CENIMAT|I3N

Ink-jet printing of amorphous oxide semiconductors for high performance TFTs

CENIMAT|I3N / Materials for Electronics, Optoelectronics and Nanotechnologies Group

UNINOVA







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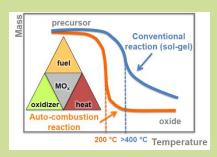
PhD Student

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Objectives

- ☐ Development of indium free amorphous metal oxide semiconductors produced by solution process (ZTO-based semiconductors).
- ☐ Deposition by Spin-coating, Spray-Coating and Inkjet printing technique.
- ☐ Fabricate high-performance TFTs with (post-)processing temperature compatible with flexible and low cost substrates such as polymers or paper.
- ☐ Demonstrate circuit integration capability fabricating a flexible n-type inverter circuit using ZTO-based TFTs produced by ink-jet.

Auto-Combustion Reaction

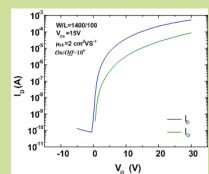


Amorphous ZTO Thin Film

100 nm

Pixdro - Piezo MEMS DOD

Electrical Characterization of TFT



Methodology

- 1. Materials synthesis and formulations. Solutions characterization
- · Choice of adequate ZTO precursors considering the combustion synthesis route, and adequate solvents and other additives considering the deposition technique
- Characterization of ZTO solution (DSC, TG and Rheology)

2. Deposition and characterization of thin films

- Tuning of deposition parameters for spin- and spray-coating and inkjet printing
- Thin film characterization (SEM, EDS, AFM, XRD, FTIR, PL, TEM, XPS)
- TFTs and inverters fabrication and characterization
- Shadow masks, optical lithography, simultaneous deposition + patterning (inkjet)
- Static and dynamic electrical measurements, bias and illumination stress

Expected Results

- ZTO-based amorphous semiconductors produced at low temperature (T<300 °C), exhibiting good uniformity and reproducibility up to 2.5x2.5 cm substrate areas and good stability over time.
- Solution-processed ZTO-based TFTs with μ >10 cm²/Vs and ΔV_{τ} <2 V under negative bias illumination stress.
- N-type inverters operating above 10 kHz based on transparent ZTO TFTs produced by inkjet on flexible substrates.







